

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) <b>PTO</b> <b>TWI-12810</b>			Application Number <b>NEW</b>		
	Applicant(s) <b>Allan Rosencwaig</b>					
	Filing Date <b>HEREWITH</b>			Group Art Unit <b>UNKNOWN</b>		

11050 U.S. PTO  
09/939817  
08/27/01

### U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
X-3	A	4,999,014	03/12/1991	Gold et al	356	382	05/04/1989
	B	5,042,951	08/27/1991	Gold et al	356	369	09/19/1989
	C	5,131,752	07/21/1992	Yu et al	356	369	06/28/1990
	D	5,620,556	04/15/1997	Henck	438	8	02/08/1995
X-3	E	5,900,939	05/04/1999	Aspnes et al	356	369	06/17/1998
X-3	F	6,085,002	07/04/2000	Qiu et al	385	52	03/16/1998

### FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

### OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

X-3	G	G.M.W. Kroesen et al., "Nonintrusive wafer temperature measurement using <i>in situ</i> ellipsometry," <i>J. Appl. Phys.</i> , Vol. 69, No. 5, 1 March 1991, pp. 3390 – 3392.
X-3	H	C.T. Yu et al., "Using In Situ Ellipsometry for Film Thickness Endpoint Control," <i>Semiconductor International</i> , May 1991, pp. 166 – 169.
X-3	I	M. Haverlag et al., "Ellipsometric study of silicon surface damage in electron cyclotron resonance plasma etching using CF <sub>4</sub> and SF <sub>6</sub> ," <i>Appl. Phys. Lett.</i> , Vol. 16, No. 24, 14 December 1992, pp. 2875 – 2877.
X-3	J	M. Haverlag et al., " <i>In situ</i> ellipsometry and reflectometry during etching of patterned surfaces: Experiments and simulations," <i>J. Vac. Sci. Technol. B</i> , Vol. 10, No. 6, Nov/Dec 1992, pp. 2412 – 2418.
X-3	K	N. Blayo et al., "Ultraviolet-visible ellipsometry for process control during the etching of submicrometer features," <i>J. Opt. Soc. Am. A</i> , Vol. 12, No. 3, March 1995, pp. 591 – 599.
X-3	L	N. Blayo et al., "New Applications of Ellipsometry for Materials Characterization and VLSI Device Process Control," <i>The Electrochemical Society Proceedings</i> , Vol. 94-33, pp. 207 – 216.
X-3	M	S.A. Henck, " <i>In situ</i> real-time ellipsometry for film thickness measurement and control," <i>J. Vac. Sci. Technol. A</i> , Vol. 10, No. 4, Jul/Aug 1992, pp. 934-938.
X-3	N	R. W. Collins, "Automatic rotating element ellipsometers: Calibration, operation, and real-time applications," <i>Rev. Sci. Instrum.</i> , Vol. 61, No. 8, August 1990, pp. 2029 – 2062.
X-3	O	Copy of U.S. Patent Application No. 09/575.295, filed May 29, 2000, by inventors Lanhua Wei et al., entitled "Monitoring Temperature and Sample Characteristics Using a Rotating Compensator Ellipsometer." 17 pages of application, and 3 pages of informal drawings.

Examiner: <i>X-3</i>	Date Considered: <i>8-19-02</i>
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	